SPECIFICATION

Device Name : High Voltage Silicon Diode

Type Name : ESJA04-02A

Spec. No. :

Fuji Electric Co.,Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED		Fuji Electric Co.,Ltd.
DRAWN					
CHECKED				DWG.NO.	

1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA04-02A made by FUJI ELECTRIC CO.,LTD.

2. OUT VIEW

Shape and dimensions are described in Fig.3.

3. IDENTIFICATION

The diode shall be marked with Cathode Mark.

4. RATINGS AND CHARACTERISTICS

4.1 ABSOLUTE MAX. RATINGS. (Ta=25 ℃ unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		V_{RRM}	2	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	I_{FSM}	0.3	Apeak
Average forward current.	50Hz Sine Wave	I_{AV}	1	mA
Allowable junction temperature.		Tj	120	℃
Storage temperature range.		Tstg	-40~120	℃
Allowable operating case temperature.		Tc	100	℃

4.2 ELECTRICAL CHARACTERISTICS (Ta=25 ℃ unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	IF=10mA	VF	12	V
Maximum reverse current	VR= 2kV	IR_1	2	μA
Maximum reverse current	VR= 2kV, 100℃	IR_2	5	μA
Maximum reverse recovery time	IF=2mA, IR=4mA	trr	0.08	μS
Maximum junction capacitance	f=1MHz, VR=0V	Cj	3	pF

4.3 MECHANICAL CHARACTERISTICS

Weight : Ca. 0.2 gr.

Vibration proof : 5 G

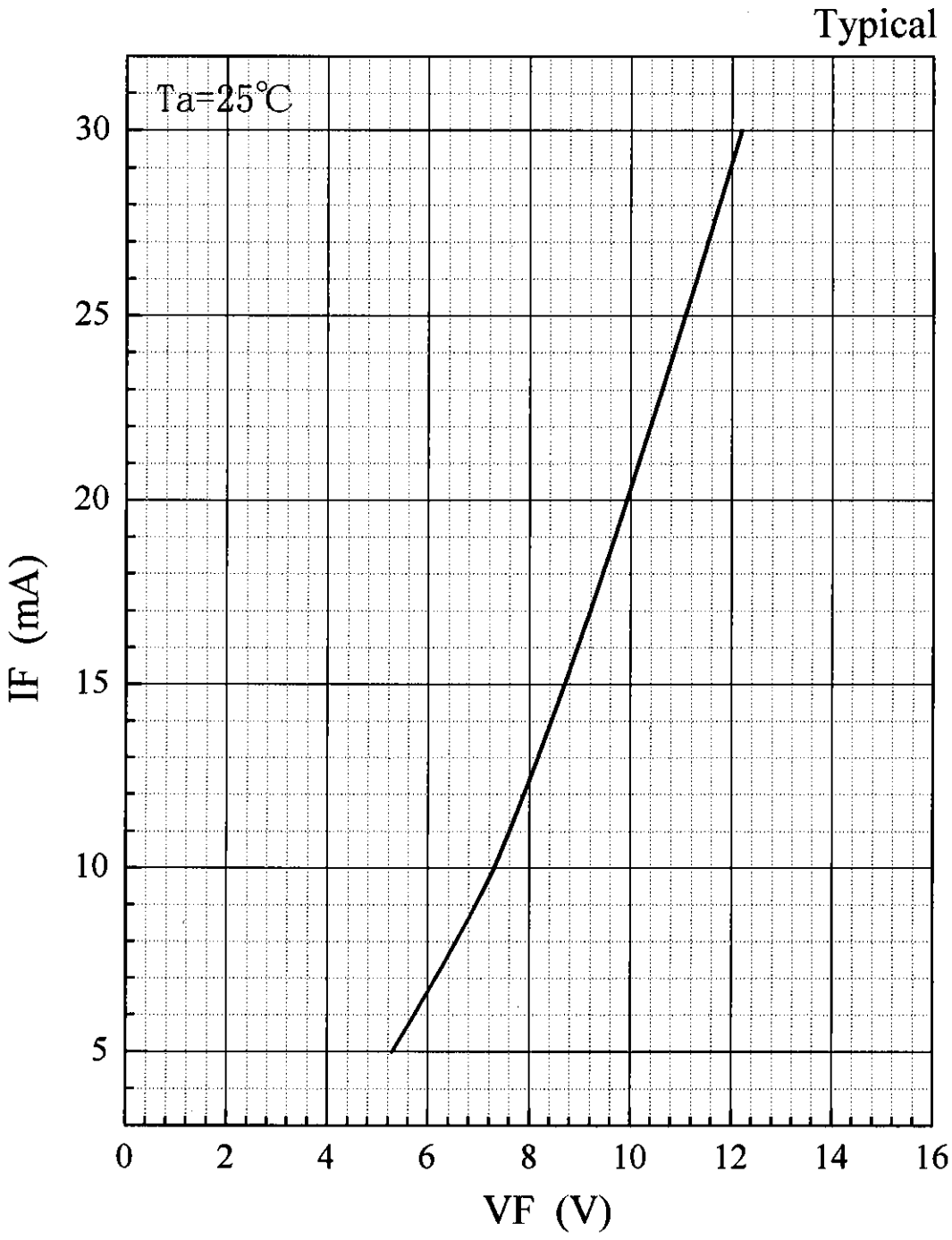


Fig.1 Forward characteristic[VF-IF]

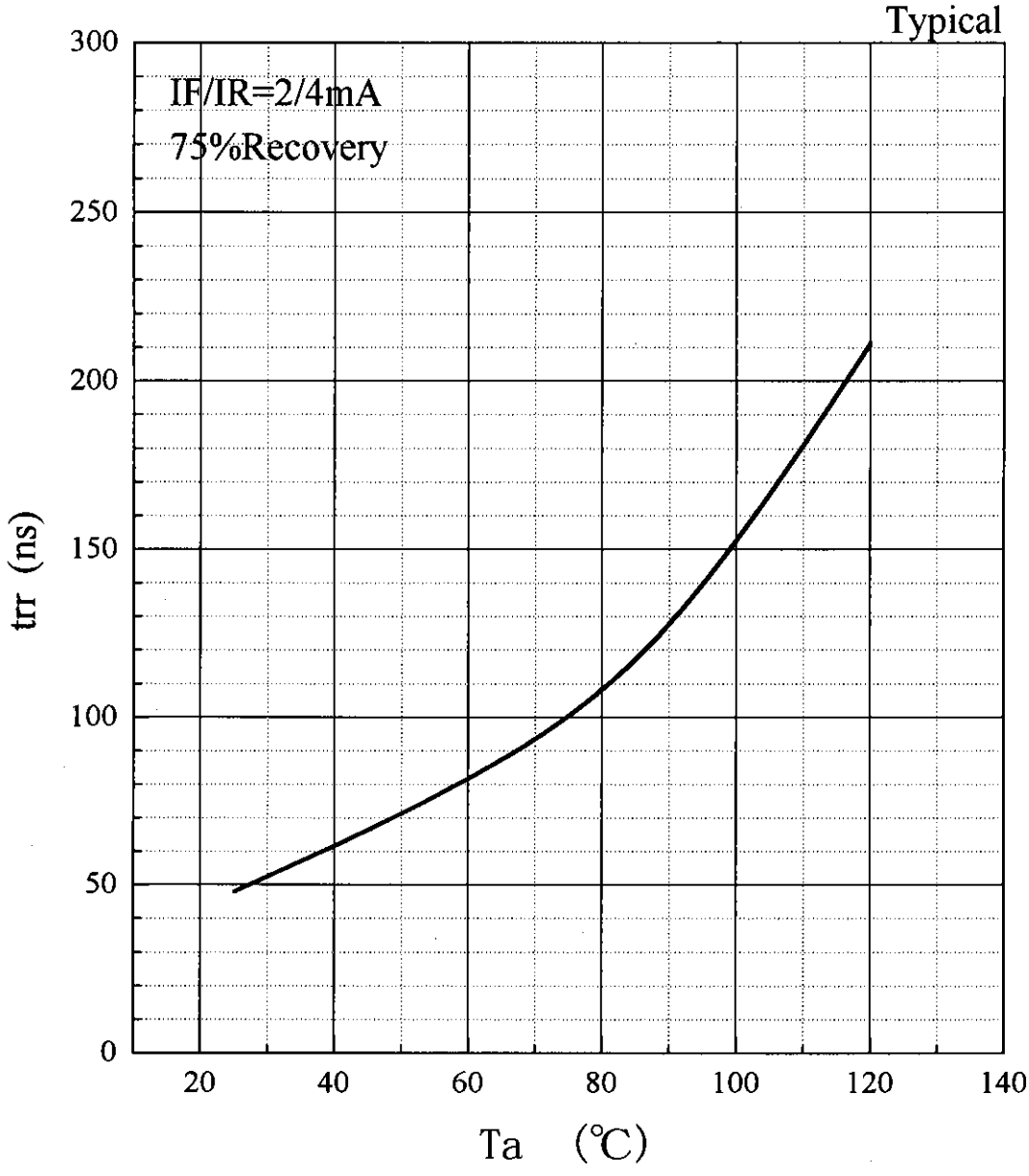


Fig.4 Reverse recovery time characteristic[Ta-trr]

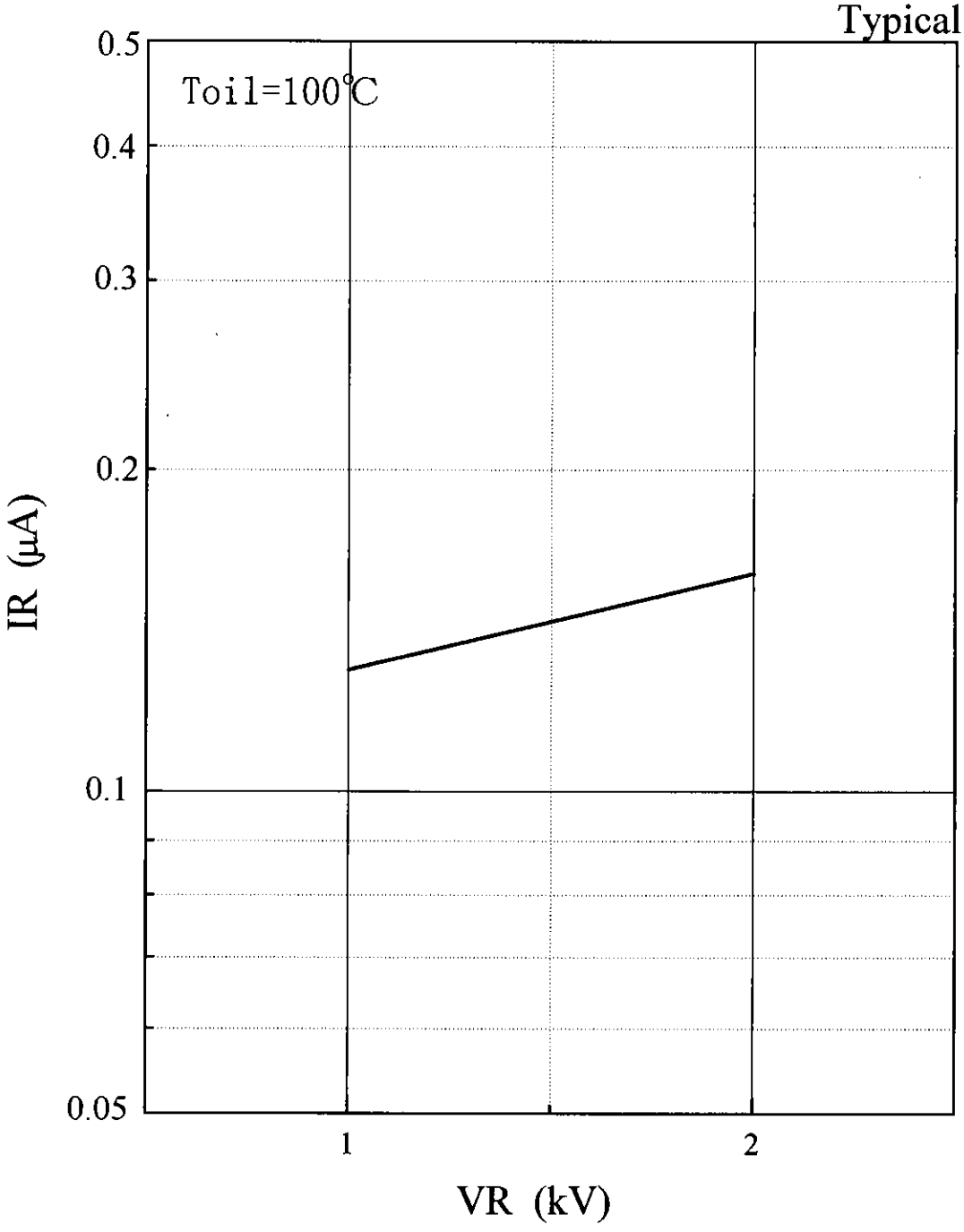


Fig.2 Reverse characteristic[VR-IR]

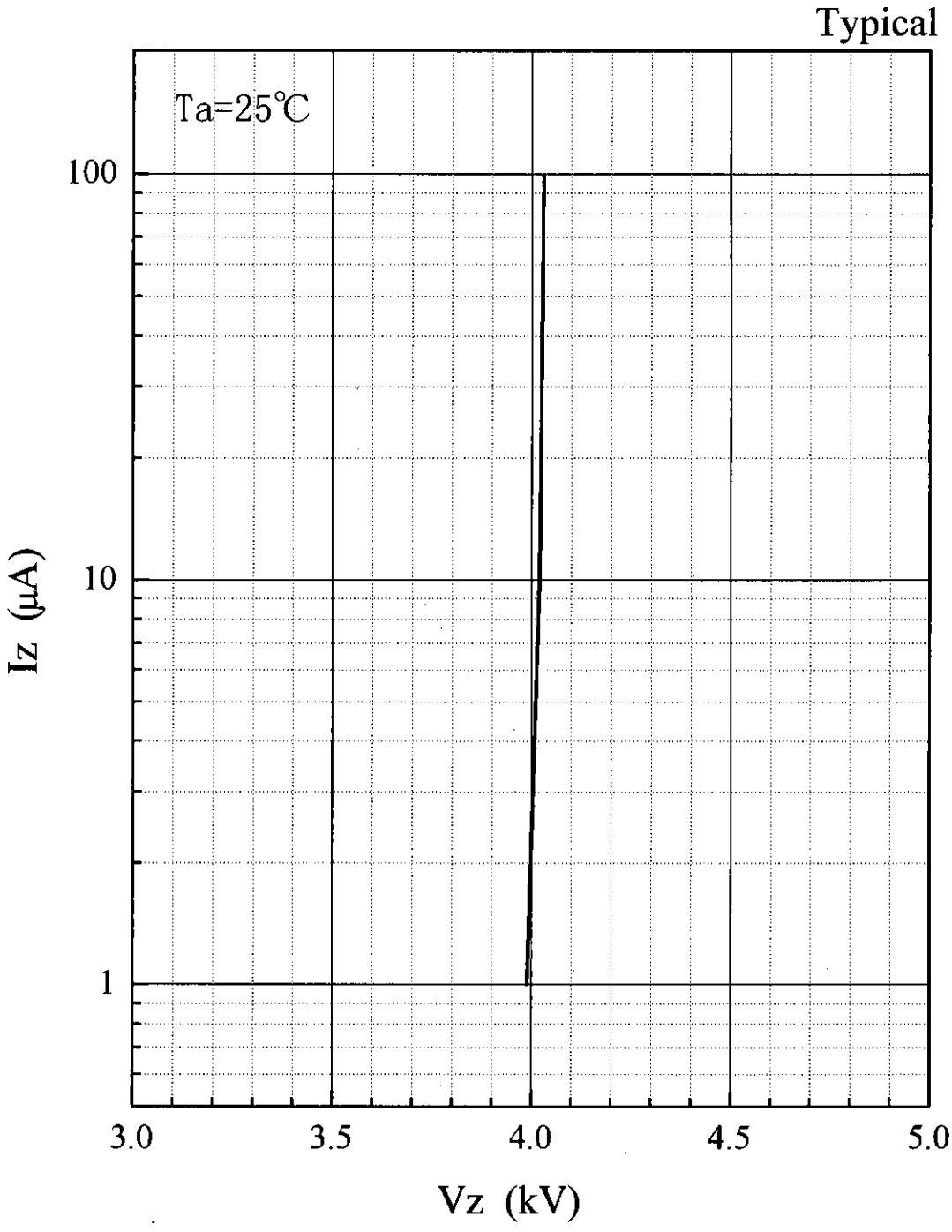
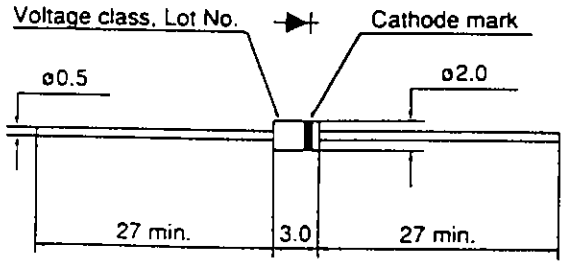


Fig.3 Avalanche characteristic[Vz-Iz]

Dimensions Unit : mm

ESJA04-□□A



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